

(09) Nitride Electronics

Co-chairs

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DETAILED PROGRAMME**Wednesday :14.12.2016****Session I : 16.00-18.00**

16:00-16:30 Invited Talk (1)	<u>MayankShrivastava</u>	ABS-Email-ICYRAM
16:30-17:00 Invited Talk (2)	<u>Praveen Kumar</u>	ABS-Email-ICYRAM InxGa1-xN nanostructures for new generation renewable energy and sensor applications
17:00-17:15 Oral (1)	<u>Pallabi Pramanik</u> Sayantani Sen Chirantan Singha A. Bhattacharyya	ABS-180-ICYRAM AlGa _N Nanorods Grown by Molecular Beam Epitaxy
17:15-17:30 Oral (2)	<u>Anisha Kalra</u> Shashwat Rathkanthiwar Swanand Solanke Rangarajan Muralidharan Srinivasan Raghavan Digbijoy Nath	ABS-750-ICYRAM Highest Responsivity in III-nitride sub-260 nm Photodetectors
17:30-17:45 Oral (3)	<u>Govind Gupta</u> Shibin Krishna Alka Sharma Neha Aggarwal Sudhir Husale	ABS-330-ICYRAM Ultrafast Nitride based broadband photo-detector with Enhanced Photo-responsivity
17:45-18:00 Oral (4)	<u>Harsh Gupta</u> Santanu Ghosh Ravi K Bommali Pankaj Srivastava, Alejandro F Braña de Cal Rafael Pérez Casero	ABS-209-ICYRAM Enhancing efficiency of c-Si solar cell by using Silicon rich silicon nitride (SRSN) films as Anti-reflection coating

Thursday :15.12.2016**Session II : 12.00-13.15**

12:00-12:30 Invited Talk (3)	<u>Poornendu Chaturvedi</u>	ABS-Email-ICYRAM Ga _N Microwave Devices for Defence
12:30-13:00 Invited Talk (4)	<u>Manvi Agarwal</u>	ABS-Email-ICYRAM

13:00-13:15 Oral (5)	<u>Monu Mishra</u> Abhiram Gundimeda Shibin Krishna Neha Aggarwal Govind Gupta	ABS-331-ICYRAM Photoemission analysis of surface modified GaN nanostructures induced via wet chemical etching
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Thursday : 15.12.2016
Session III : 16.00-18.00

16:00-16:30 Invited Talk (5)	<u>Yogesh Singh Chauhan</u>	ABS-Email-ICYRAM Modeling of high power and high frequency GaN-HEMTs using ASM-HEMT compact model
16:30-17:00 Invited Talk (6)	<u>Basanta Roul</u> S B Krupanidhi	ABS-Email-ICYRAM III-nitride Epitaxial Heterostructures for Light Emitting Diode Applications
17:00-17:15 Oral (6)	<u>Adarsh Nigam</u> Mahesh Kumar	ABS-535-ICYRAM Device Modeling and Simulation of AlGaIn/GaN High Electron Mobility Transistor on Si Substrate
17:15-17:30 Oral (7)	<u>Neha Aggarwal</u> Shibin Krishna Alka Sharma K. K. Maurya Manju Singh Rajib Rakshit Nita Dilawar Sudhir C Husale Govind Gupta	ABS-410-ICYRAM Highly sensitive visible-blind GaN Nanostructure based UV Photodetector for fast optical switching
17:30-17:45 Oral (8)	<u>Shibin Krishna</u> Neha Aggarwal K. K Maurya Govind Gupta	ABS-521-ICYRAM Epitaxial growth of GaN/AlN and InGaIn/GaN/AlN heterostructures on Si (111) via Plasma Assisted Molecular Beam Epitaxy
17:45-18:00 Oral (9)	<u>Sheikh Aamir Ahsan</u> Sudip Ghosh Avirup Dasgupta Sourabh Khandelwal Yogesh Singh Chauhan	ABS-347-ICYRAM ASM-HEMT: Advanced SPICE Model for Gallium Nitride High Electron Mobility Transistors

Poster Session:**Wednesday : 14.12.2016 : Time: 10:15 - 13:15**

09-Poster-01	Varun Singh Nirwal Koteswara Rao Peta	ABS-81-ICYRAM Reverse Leakage Transport Mechanism in GaN Schottky Diode
09-Poster-02	Sayantani Sen Pallabi Pramanik Chirantan Singha Anirban Bhattacharyya	ABS-213-ICYRAM Effect of compositional inhomogeneities in AlGa _N alloys on metal-semiconductor contacts
09-Poster-03	G Venkata Rao T.V. Rajesh, M. Kumar S.V. Jagadeesh Chandra	ABS-275-ICYRAM Effect of Nitride layer on the Interfacial Engineering at HfO ₂ /Ge Stacks for MOS devices
09-Poster-04	Lalit Goswami Rajeshwari Pandey Neha Aggarwal Shibin Krishna Alka Sharma Sudhir Husale Govind Gupta	ABS-362-ICYRAM Realization of low voltage operable UV-Detectors using GaN Nanostructures by PA-MBE
09-Poster-05	S Sinha Aditi , S K Sinha R Mukhiya, R Sharma V K Khanna	ABS-392-ICYRAM Optimization of Aluminum Nitride Sensing Film using Magnetron Assisted Pulsed DC Reactive Sputtering
09-Poster-06	Shubhendra Jain Shibin Krishna Neha Aggarwal Rahul Kumar Sudhir C Husale Vinay Gupta Govind Gupta	ABS-581-ICYRAM Effect of symmetric & asymmetric metal-semiconductor-metal structure on the opto-electrical characteristics of epitaxial GaN films
09-Poster-07	Greeshma Chandan Rohit Panth Shruti Mukundan Basanta Roul S B Krupanidhi	ABS-667-ICYRAM Reciprocal space mapping of InGa _N epilayers on bare and nitrided Si (111) by PAMBE